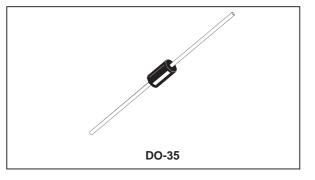


# **BAT41**

# SMALL SIGNAL SCHOTTKY DIODE

#### DESCRIPTION

General purpose metal to silicon diode featuring very low turn-on voltage and fast switching. This device has integrated protection against excessive voltage such as electrostatic discharges.



#### **ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit	
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	100	V	
١ <sub>F</sub>	Forward Continuous Current*	100	mA	
I <sub>FRM</sub>	Repetitive Peak Forward Current*	$ \begin{array}{l} \mbox{tritive Peak Forward Current}^{*} & t_{p} \leq \mbox{1s} \\ \delta \leq \mbox{0.5} \end{array} $		mA
I <sub>FSM</sub>	Surge non Repetitive Forward Current* $t_p \le 10ms$		750	mA
P <sub>tot</sub>	Power Dissipation* T <sub>a</sub> = 95°C		100	mW
T <sub>stg</sub> Tj	Storage and Junction Temperature Range		- 65 to +150 - 65 to +125	°C ℃
TL	Maximum Lead Temperature for Soldering du from Case	230	°C	

#### THERMAL RESISTANCE

Symb	Test Conditions	Value	Unit
R <sub>th(j-a</sub>	Junction-ambient*	300	°C/W

### **ELECTRICAL CHARACTERISTICS**

## STATIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
V <sub>BR</sub>	T <sub>j</sub> = 25°C	I <sub>R</sub> = 100μA		100			V
V <sub>F</sub> * *	T <sub>j</sub> = 25°C	$I_F = 1 m A$			0.4	0.45	V
	T <sub>j</sub> = 25°C	I <sub>F</sub> = 200mA				1	
I <sub>R</sub> * *	T <sub>j</sub> = 25°C		V <sub>R</sub> = 50V			0.1	μA
	T <sub>j</sub> = 100°C					20	

# DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
С	$T_j = 25^{\circ}C$	$V_R = 1V$	f = 1MHz		2		pF

\* On infinite heatsink with 4mm lead length \* \* Pulse test:  $t_p\!\leq\!300\mu s~\delta\!<\!2\%$  .

10~2

0

25



10<sup>3</sup>

10<sup>2</sup>

10

1

10<sup>-1</sup>

10<sup>-2</sup>

10<sup>2</sup>

0

I<sub>Π</sub> (μΑ)

I<sub>f</sub> (mA)

Fig. 1: Forward current versus forward voltage at different temperatures (typical values).

⊊Ťi

¯τ<sub>j</sub> =

= <u>∑</u> T<sub>j</sub> =

1

T<sub>i</sub>

100

125

75

125°C

25°C

55°C

(V) ٧<sub>F</sub>

1.2 1.4

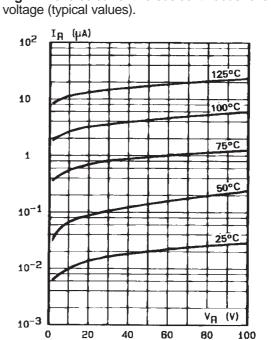
Fig. 3: Reverse current versus junction temperature.

0.2 0.4 0.6 0.8

90 % confidence V<sub>R</sub> = 50 V 10 max typ. 1 10<sup>-1</sup> (°C)

50

Fig. 4: Reverse current versus continuous reverse



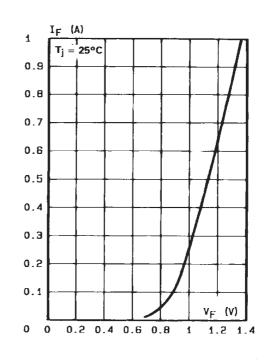


Fig. 2: Forward current versus forward voltage (typical values).

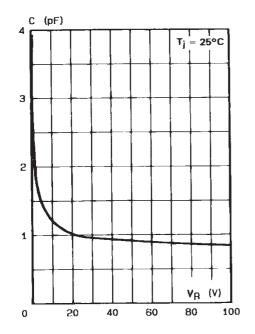
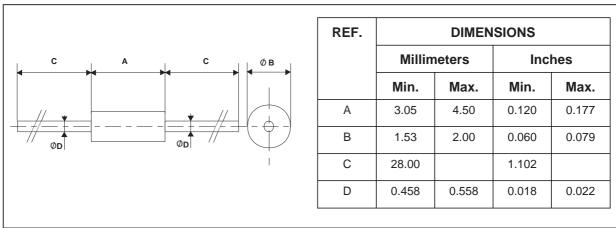


Fig. 5: Capacitance C versus reverse applied voltage  $V_{_{\rm R}}$  (typical values).

#### PACKAGE MECHANICAL DATA

DO-35



Cooling method : by convection and conduction Marking: clear, ring at cathode end. Weight: 0.15g

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

http://www.st.com

**/**/